| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| S1 | 656 | (438/194,285,574,767).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/14 07:53 |
| S2 | 656 | (438/194,285,574,767).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/12 17:23 |
| S3 | 610 | S2 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/12 17:23 |
| S4 | 656 | (438/194,285,574,767).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/13 16:38 |
| S5 | 610 | S4 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:38 |
| S6 | 67 | S5 and (gallium adj nitride or GaN) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:07 |
| S7 | 1 | S6 and (atomic adj nitrogen) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 17:05 |
| S8 | 43 | S6 and (electrode) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:42 |

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| S9 | 35 | S8 and (nitrid$5) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:55 |
| S10 | 1 | S8 and (nitriding) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/13 16:55 |
| S11 | 689 | (438/181,182,572,775,777).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/14 07:54 |
| S16 | 650 | S11 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 08:00 |
| S17 | 22 | S16 and (gallium adj nitride or GaN) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 08:20 |
| S18 | 17 | S17 and (electrode) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:10 |
| S19 | 1 | S18 and (atomic near nitrogen) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 08:03 |
| S20 | 35905 | (gallium adj nitride) or GaN | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:11 |

| S21 | 9287 | S20 and electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:11 |
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| S22 | 220 | S21 and (atomic adj nitrogen or nitriding) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:12 |
| S23 | 50 | S22 and (atomic adj nitrogen) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:40 |
| S24 | 9 | S23 and nitriding | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:15 |
| S25 | 7 | S24 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:16 |
| S26 | 199 | S22 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 09:41 |
| S27 | 35905 | (gallium adj nitride) or GaN | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:01 |
| S28 | 9287 | S27 and electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:01 |

| S29 | 220 | S28 and (atomic adj nitrogen or nitriding) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:01 |
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| S30 | 50 | S29 and (atomic adj nitrogen) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:01 |
| S31 | 9 | S30 and nitriding | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:01 |
| S32 | 656 | (438/194,285,574,767).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/14 15:09 |
| S33 | 610 | S32 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:09 |
| S34 | 2 | S33 and (surface adj3 stabiliz$5 near method) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 15:12 |
| S35 | 24197 | (gallium adj nitride) or (GaN) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/18 08:31 |
| S36 | 10865 | S35 and (source or gate or drain) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/18 08:31 |
| S37 | 3695 | S36 and ((nitride or nitrogen or nitridation or nitr$4) same surface) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/18 08:34 |

| S38 | 760 | S36 and ((nitrogen or nitridation) with surface) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/18 08:34 |
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| S39 | 359 | S38 and (transistor or (integrated adj circuit)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/18 08:36 |
| S40 | 343 | S39 and (@ad<"20040225" or @rlad<"20040225") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/18 10:10 |
| S41 | 50 | S35 and ((surface adj treatment) with nitrid$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/18 08:39 |
| S42 | 35960 | (gallium adj nitride) or GaN | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/19 15:04 |
| S43 | 9308 | S42 and electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/19 15:04 |
| S44 | 221 | S43 and (atomic adj nitrogen or nitriding) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/19 15:04 |
| S45 | 50 | S44 and (atomic adj nitrogen) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/19 16:11 |
| S46 | 658 | (438/194,285,574,767).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/19 15:33 |

| S47 | 612 | S46 and @ad<"20040225" | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/19 15:33 |
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| S48 | 68 | S47 and (gallium adj nitride or GaN) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/20 11:32 |
| S49 | 44 | S48 and (electrode) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/19 15:42 |
| S50 | 58 | S48 and (source or gate or drain) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/19 15:43 |
| S51 | 11 | (atomic adj nitrogen) with (produce or generate or create) same (nitrogen near gas) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/19 16:26 |
| S52 | 11 | S51 and (@ad<"20040225" or rlad<"20040225") | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/19 16:19 |
| S53 | 88 | (atomic adj nitrogen) with (produce or generate or create) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/19 16:19 |
| S54 | 88 | S53 and (@ad<"20040225" or rlad<"20040225") | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/19 16:19 |

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| S55 | 11 | atomic adj nitrogen with (produce or generate or create) same (nitrogen near gas) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/19 16:26 |
| S56 | 658 | (438/194,285,574,767).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/20 11:33 |
| S57 | 612 | S56 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 11:33 |
| S58 | 6312206 | S57 and (aluminum adj nitride or AlN) or (aluminum or Al) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 11:34 |
| S59 | 45 | S57 and (aluminum adj nitride or AlN) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 11:56 |
| S60 | 230 | S57 and (aluminum adj nitride or AlN or aluminum) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 11:56 |
| S61 | 184 | S60 and (gate or source or drain) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 13:47 |
| S62 | 658 | (438/194,285,574,767).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/20 13:48 |

| S63 | 612 | S62 and @ad<"20040225" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 13:48 |
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| S64 | 230 | S63 and (aluminum adj nitride or AlN or aluminum) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 13:48 |
| S65 | 184 | S64 and (gate or source or drain) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 13:48 |
| S66 | 45 | S65 and (gallium adj nitride or GaN) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 14:40 |
| S67 | 24227 | (gallium adj nitride) or (GaN) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 14:41 |
| S68 | 10883 | S67 and (source or gate or drain) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 14:41 |
| S69 | 762 | S68 and ((nitrogen or nitridation) with surface) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/21 10:46 |
| S70 | 361 | S69 and (transistor or (integrated adj circuit)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 14:41 |
| S71 | 345 | S70 and (@ad<"20040225" or @rlad<"20040225") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 14:41 |

| S72 | 11 | S71 and (insulation adj layer) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/20 14:41 |
|---|---|---|---|---|---|---|
| S73 | 24281 | (gallium adj nitride) or (GaN) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/21 10:47 |
| S74 | 10922 | S73 and (source or gate or drain) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/21 10:47 |
| S75 | 114 | S74 and (nitrogen with implantation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/21 11:11 |